

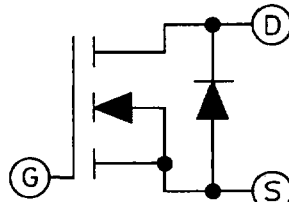
ABSOLUTE MAXIMUM RATINGS			
PARAMETER	SYMBOL		UNITS
Drain-source Volt.(1)	V _{DSS}	600	V _{dc}
Drain-Gate Voltage (R _{GS} =1.0M Ω) (1)	V _{DGR}	600	V _{dc}
Gate-Source Voltage Continuous	V _{GS}	± 20	V _{dc}
Drain Current Continuous (T _c = 25°C)	I _D	1.5	A _{dc}
Drain Current Pulsed(3)	I _{DM}	6.0	A
Total Power Dissipation	PD	50	W
Power Dissipation Derating > 25°C		0.4	W/°C
Operating & Storage Temp.	T _J /T _{stg}	-55 TO +150	°C
Thermal Resistance	R _{thJc}	2.5	°C/W
Max. Lead temperature	TL	300	°C

ELECTRICAL CHARACTERISTICS T _c = 25°C (UNLESS OTHERWISE SPECIFIED)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Drain-source Breakdown Volt.	V _{(BR)DSS}	V _{GS} =0V I _D =250 μ A	600	-	-	V
Gate Threshold Voltage	V _{GS(TH)}	V _D =V _{GS} I _D =250 μ A	2.0	-	4.0	V
Gate Source Leakage	I _{GSS}	V _{GS} = ± 20 V	-	-	100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _D =MAX. RATING V _{GS} =0	-	-	100	μ A
		V _D =0.8 MAX. RATING V _{GS} =0 T _J =125°C	-	-	2.0	mA
Static Drain-Source On-State Resistance(1)	R _{DS(ON)}	V _{GS} =10 V I _D =0.5A	-	-	6.0	Ω
Forward Trans-Conductance (2)	g _{fs}	V _D \geq 2.5V I _D =0.5A	0.5	-	-	S(U)
Input Capacitance	C _{ISS}	V _{GS} =0V V _D =25 V f=1.0 MHz	-	-	650	pF
Output Capacitance	C _{OSS}		-	-	125	pF
Reverse Transfer Capacitance	C _{RSS}		-	-	50	pF
Turn-On Delay	t _{d(on)}	V _D =25V R _s =50 Ω I _D =0.5A	-	-	15	ns
Rise Time	t _r	(MOSFET switching times are essentially independent of operating temp.)	-	-	15	ns
Turn-Off Delay	t _{d(off)}		-	-	100	ns
Fall Time	t _f		-	-	25	ns

SOURCE-DRAIN DIODE RATINGS & CHARACT. T _c = 25°C (UNLESS OTHERWISE SPECIFIED)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Diode Forward Voltage (2)	V _{SD}	I _F =1.5A, V _{GS} =0V T _c =+25°C	-	-	1.5	V
Reverse Recovery Time	t _{rr}	T _c =+25°C I _F =1.5A	-	450	-	ns

TERMINAL CONNECTIONS			
G		H	
1	GATE	1	DRAIN
2	DRAIN	2	SOURCE
3	SOURCE	3	GATE

SCHEMATIC



(1) T_J = 25°C to 150°C.
 (2) Pulse test: Pulse Width < 300 μ s, Duty Cycle < 2%.
 (3) Repetitive Rating: Pulse Width limited By Max. junction Temperature.

600V, 1.5A, 6.0 Ω

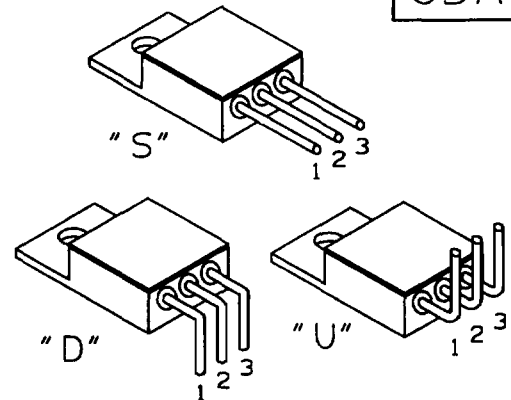
SDF 1NA60 JAA
 SDF 1NA60 JAB
 SDF 1NA60 JDA

FEATURES

- RUGGED PACKAGE
- HI-REL CONSTRUCTION
- CERAMIC EYELETS; JAA, JAB
- LEAD BENDING OPTIONS
- COPPER CORED 52 ALLOY PINS
- LOW IR LOSSES
- LOW THERMAL RESISTANCE
- OPTIONAL MIL-S-19500 SCREENING

STANDARD BEND CONFIGURATIONS

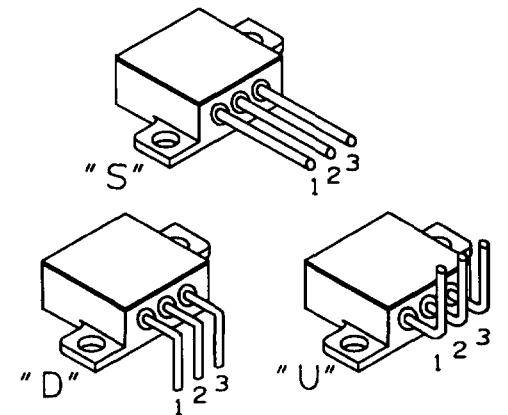
JAA
 JDA



(CUSTOM BEND OPTIONS AVAILABLE)

STANDARD BEND CONFIGURATIONS

JAB



(CUSTOM BEND OPTIONS AVAILABLE)